

Schottky Diode

$$V_{RRM} = 60 \text{ V}$$

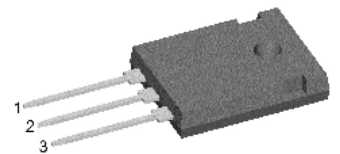
$$I_{FAV} = 2 \times 20 \text{ A}$$

$$V_F = 0.46 \text{ V}$$

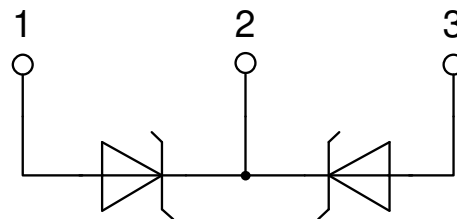
High Performance Schottky Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DSSK40-006B



Backside: cathode



Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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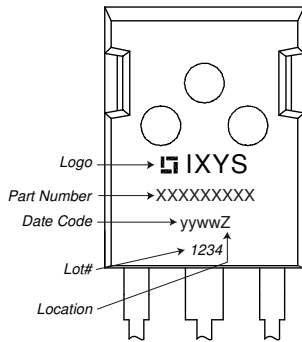


Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					60	V
V_{RRM}	max. repetitive reverse blocking voltage					60	V
I_R	reverse current, drain current	$V_R = 60\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		20	mA
		$V_R = 60\text{ V}$		$T_{VJ} = 100^\circ\text{C}$		100	mA
V_F	forward voltage drop	$I_F = 20\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		0.50	V
		$I_F = 40\text{ A}$				0.67	V
		$I_F = 20\text{ A}$		$T_{VJ} = 125^\circ\text{C}$		0.46	V
		$I_F = 40\text{ A}$				0.62	V
I_{FAV}	average forward current	$T_C = 135^\circ\text{C}$	rectangular	$T_{VJ} = 150^\circ\text{C}$		20	A
			d = 0.5				
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		0.31	V
r_F	slope resistance					6.9	mΩ
R_{thJC}	thermal resistance junction to case					1.1	K/W
R_{thCH}	thermal resistance case to heatsink			0.25			K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		115	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_R = 0\text{ V}$		$T_{VJ} = 45^\circ\text{C}$		500	A
C_J	junction capacitance	$V_R = 12\text{ V}$	f = 1 MHz	$T_{VJ} = 25^\circ\text{C}$		888	pF



Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			70	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking



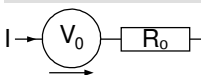
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSSK40-006B	DSSK40-006B	Tube	30	479136

Similar Part	Package	Voltage class
DSB60C60HB	TO-247AD (3)	60
DSB60C60PB	TO-220AB (3)	60

Equivalent Circuits for Simulation

** on die level*

$T_{VJ} = 150^{\circ}C$

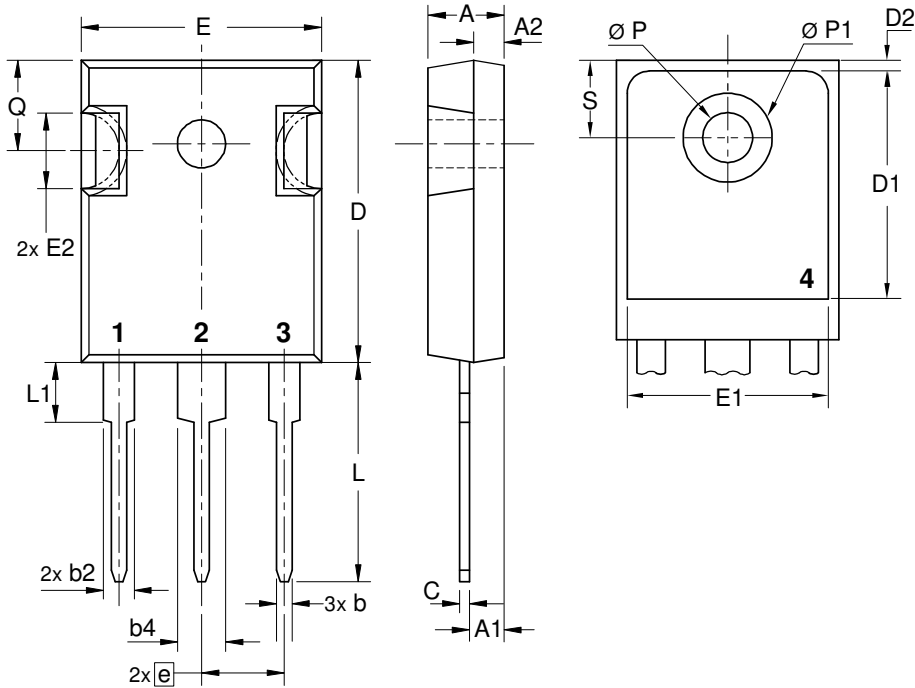


Schottky

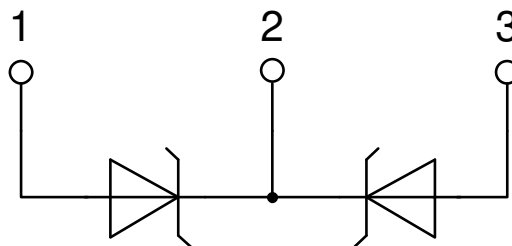
$V_{0 \max}$	threshold voltage	0.31	V
$R_{0 \max}$	slope resistance *	4.4	mΩ



Outlines TO-247



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215 BSC		5.46 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212		5.38	
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39





Schottky

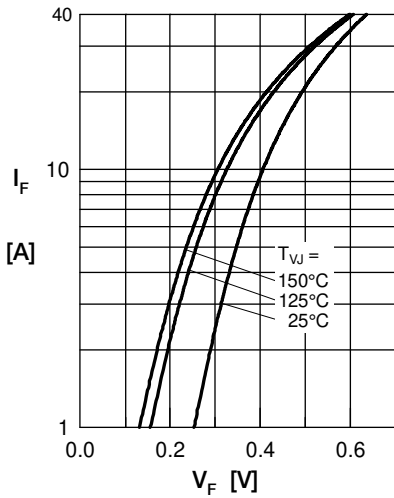


Fig. 1 Max: forward voltage drop characteristics

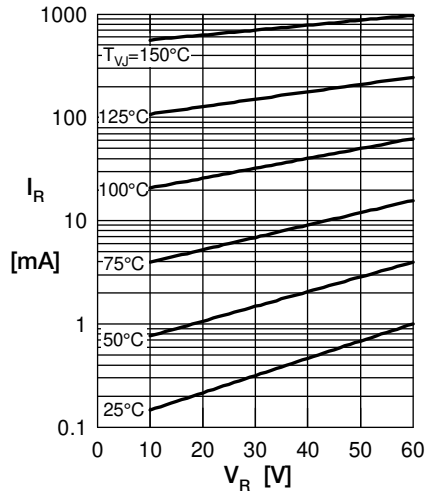


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

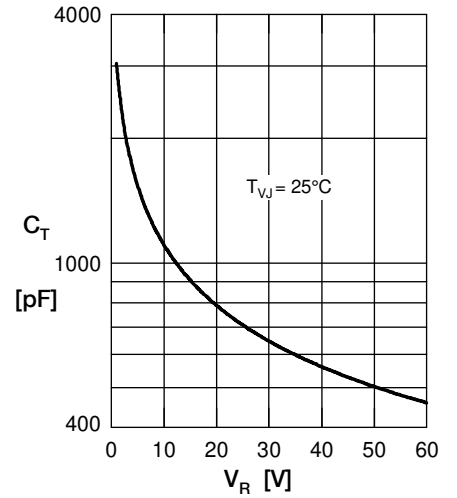


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

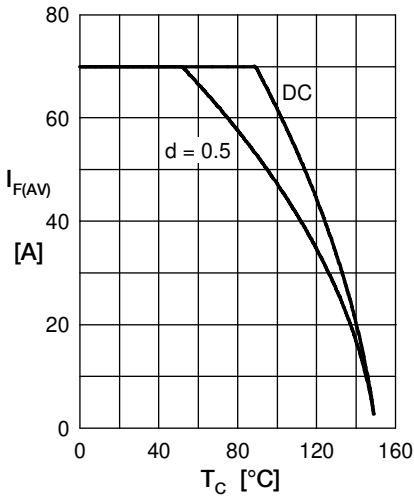


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temp: T_C

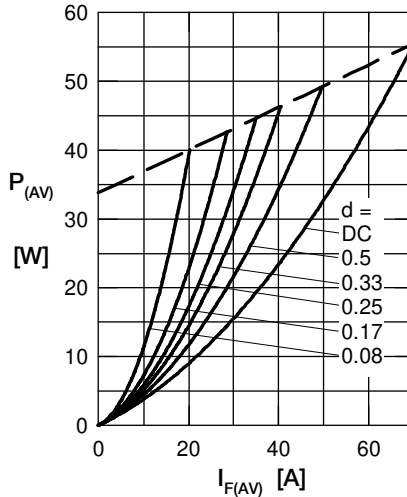


Fig. 5 Forward power loss characteristics

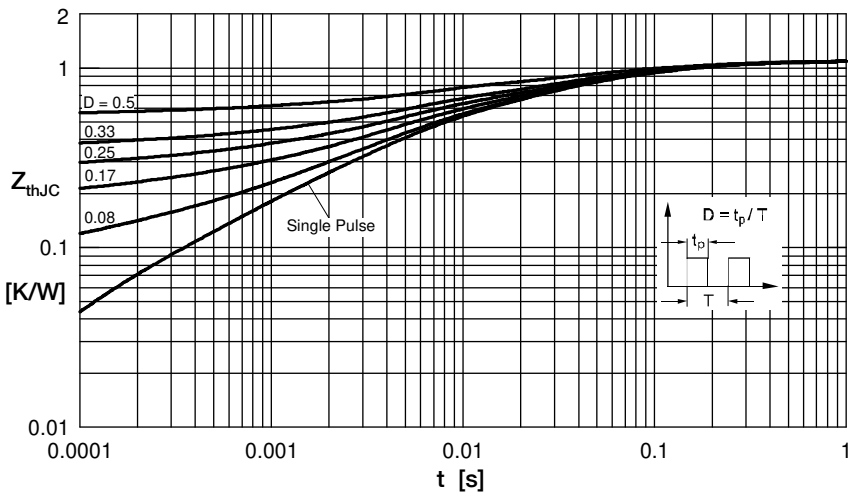


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode